

NTHL080N120SC1A

Silicon Carbide MOSFET, N-Channel, 1200 V, 80 mΩ, TO247-3L

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

- High Speed Switching and Low Capacitance
- 1200V rated
- Max RDS(on) = 110mΩ at Vgs = 20V, Id = 20A
- 100% UIL Tested
- Coss = 80pF
- PFC
- Boost Inverter
- PV Charging
- Solar Inverter
- Network Power Supply
- Server Power Supply

| | Pricing (\$/Unit) | Compliance | Status | Family | Blocking Voltage BV _{DSS} (V) | I _{D(max)} (A) | R _{DS(on) Typ @ 25°C} (mΩ) | Q _g Total (nC) | Output Capacitance (pF) | T _J Max (°C) | Package Type |
|-----------------|-------------------|------------|--------|--------|--|-------------------------|-------------------------------------|---------------------------|-------------------------|-------------------------|--------------|
| NTHL080N120SC1A | 7.5097 | | Active | M1 | 1200 | 31 | 80 | 56 | 80 | 175 | TO-247-3LD |